

# BTA316A

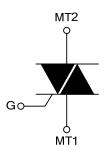
# **16A TRIACS**

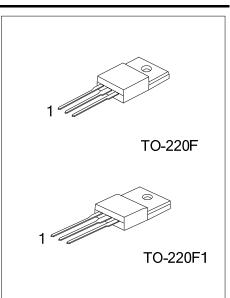
# DESCRIPTION

The UTC **BTA316A** is a 16A triacs which can be operated in 3 quadrants only, it uses UTC's advanced technology to provide customers with high commutation performances, etc.

The UTC **BTA316A** is suitable for inductive load switching operations, also can be used in ON/OFF function applications such as induction motor starting circuits, heating regulation, static relays etc.

#### SYMBOL





# ORDERING INFORMATION

Ordering	Deekege	Pin	Assignr	Deaking				
Lead Free	Halogen Free	Package	1	2	3	Packing		
BTA316AL-x-xx-TF1-T	BTA316AG-x-xx-TF1-T	TO-220F1	MT1	MT2	G	Tube		
BTA316AL-x-xx-TF3-T	BTA316AG-x-xx-TF3-T	TO-220F	MT1	MT2	G	Tube		
Note: Pin Assignment: MT1: MT1 MT2: MT2 G: Gate								
BTA316AL-x-xx-TE1-T								

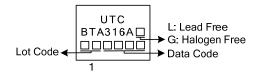
DIA310AL-X-XX-IFI-1		ł.
ŢŢŢŢŢŢ Ţ ⊂ (1)Packing Type	(1) T: Tube	
(2)Package Type	(2) TF1: TO-220F1, TF3: TO-220F	
(3)Sensitivity and type	(3) refer to SENSITIVITY AND TYPE	
(4)Voltage	(4) 6: 600V, 8: 800V	
(5)Green Package	(5) L: Lead Free, G: Halogen Free and Lead Free	
		ı.

#### SENSITIVITY AND TYPE

PART NUMBER	VOL	ΓAGE	SENSITIVITY	TYPF
PART NUMBER	600V	800V	SENSITIVITY	ITPE
BW	O	$\bigcirc$	50mA	SNUBBERLESS
CW	O	$\bigcirc$	35mA	SNUBBERLESS
SW	0	O	10mA	LOGIC LEVEL

O: Available

## MARKING



## TRIAC

# ABSOLUTE MAXIMUM RATINGS

PARAME	TER		SYMBOL	RATINGS	UNIT
RMS On-State Current (Full Sine Wave)		T <sub>C</sub> =86°C	I <sub>T(RMS)</sub>	16	А
Non Repetitive Surge Peak On-State Current (Full	F=50 Hz	t=20ms	I <sub>TSM</sub>	160	А
Cycle, T <sub>J</sub> initial=25°C)	F=60 Hz	t=16.7ms	ISM	168	А
I <sup>2</sup> t Value for Fusing	t <sub>P</sub> =10ms		l <sup>2</sup> t	144	A <sup>2</sup> s
Critical Rate of Rise of On-State Current I <sub>G</sub> =2xI <sub>GT</sub> , tr≤100ns	F=120 Hz	TJ=125°C	dl/dt	50	A/µs
Non Repetitive Surge Peak Off-State Voltage	t <sub>P</sub> =10ms	TJ=25°C	$V_{\text{DSM}}/V_{\text{RSM}}$	V <sub>DRM</sub> /V <sub>RRM</sub> +100	V
Peak Gate Current	t <sub>P</sub> =20µs	TJ=125°C	I <sub>GM</sub>	4	А
Average Gate Power Dissipation T <sub>J</sub> =125°C			P <sub>G(AV)</sub>	1	W
Operating Junction Temperature			TJ	-40~+125	°C
Storage Junction Temperatu	re		T <sub>STG</sub>	-40~+150	°C

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

# THERMAL RESISTANCES

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ <sub>JA</sub>	60	°C/W
Junction to Case (AC)	θ <sub>JC</sub>	2.1	°C/W

#### ■ ELECTRICAL CHARACTERISTICS (T<sub>J</sub>=25°C unless otherwise specified.)

# FOR SNUBBERLESS TYPE and LOGIC LEVEL TYPE (3 QUADRANTS)

PARAMETER	SYMBOL	TEST CONDIT			SW CW BW			UNIT					
	STWDUL	TEST CONDITI		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
Gate Trigger Current (Note 1)	I <sub>GT</sub>	V <sub>D</sub> =12V, R <sub>L</sub> =33Ω	1-11-111			10			35			50	mA
Gate Trigger Voltage	V <sub>GT</sub>		1-11-111			1.3			1.3			1.3	V
Gate Non-Trigger Voltage	$V_{GD}$	V <sub>D</sub> =V <sub>DRM</sub> , R <sub>L</sub> =3.3kΩ, T <sub>J</sub> =125°C	1-11-111	0.2			0.2			0.2			v
Holding Current (Note 2)	I <sub>H</sub>	I⊤=500mA				15			35			50	mA
Latching Current		I <sub>G</sub> =1.2I <sub>GT</sub>	1-111			25			50			70	mA
Latoning Current	١L	IG-I.ZIGT	П			30			60			80	mA
Critical Rate of Rise of Off-State Voltage (Note 2)	dV/dt	V <sub>D</sub> =67%V <sub>DRM</sub> , Ga Open, T <sub>J</sub> =125°C	te	40			500			1000			V/µs
(d\		(dV/dt)c=0.1V/µs, T <sub>J</sub> =125°C		8.5									A/ms
of Off-State Voltage at Commutation	ate Voltage (dl/dt)c (dV/dt)c=10V/µs,		3.0									A/ms	
(Note 2)		Without Snubber TJ=125°C					8.5			14			A/ms

Notes: 1. Minimum  $I_{GT}$  is guaranteed at 5% of  $I_{GT}$  max.

2. For both polarities of MT2 referenced to MT1.



# **STATIC CHARACTERISTICS**

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT
Peak On-State Voltage(Note 2)	V <sub>TM</sub>	I <sub>TM</sub> =22.5A, t <sub>p</sub> =380μs T <sub>J</sub> =25°C				1.55	V
Threshold Voltage(Note 2)	V <sub>TO</sub>		TJ=125°C			0.85	V
Dynamic Resistance(Note 2)	R <sub>D</sub>		TJ=125°C			25	mΩ
Repetitive Peak Off-State Current	I <sub>DRM</sub>		TJ=25°C			5	μA
	I <sub>RRM</sub>	V <sub>DRM</sub> =V <sub>RRM</sub>	TJ=125°C			2	mA

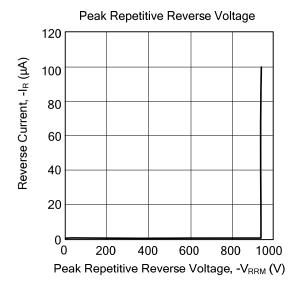
Notes: 1. Minimum  $I_{\text{GT}}$  is guaranteed at 5% of  $I_{\text{GT}}$  max.

2. For both polarities of MT2 referenced to MT1.



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# TYPICAL CHARACTERISTICS



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